

FEATURES

- Available as "HR" (high reliability) screened per MIL-PRF-19500, JANTX level. Add "HR" suffix to base part number.
- Available as non-RoHS (Sn/Pb plating), standard, and as RoHS by adding "-PBF" suffix.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak repetitive off-state voltage⁽¹⁾ ($T_J = -40$ to $+125^\circ\text{C}$) MAC219-4 MAC219-6 MAC219-8 MAC219-10	V_{DRM}	200 400 600 800	Volts
Peak gate voltage	V_{GM}	± 10	Volts
RMS on-state current (conduction angle = 360° , $T_C = 80^\circ\text{C}$)	$I_{\text{T(RMS)}}$	8.0	Amps
Peak non-repetitive surge current (1 cycle, 60 Hz)	I_{TSM}	100	Amps
Circuit fusing considerations ($t = 8.3\text{ms}$)	I^2t	35	A^2s
Peak gate power ($T_C = 80^\circ\text{C}$, pulse width = $2\mu\text{s}$)	P_{GM}	16	Watts
Average gate power ($T_C = 80^\circ\text{C}$, $t = 8.3\text{ms}$)	$P_{\text{G(AV)}}$	0.35	Watts
Peak gate trigger current (Pulse width = $1.0\mu\text{s}$)	I_{GM}	4.0	Amps
Operating junction temperature range	T_J	-40 to +125	$^\circ\text{C}$
Storage temperature range	T_{stg}	-40 to +150	$^\circ\text{C}$

Note 1: Ratings apply for open gate conditions. Thyristor devices shall not be tested with a constant current source for blocking capability such that the voltage applied exceeds the rated blocking voltage.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Maximum	Unit
Thermal resistance, junction to case	$R_{\theta\text{JC}}$	2.2	$^\circ\text{C}/\text{W}$

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ.	Max	Unit
Peak blocking current (either direction) ($V_D = \text{Rated } V_{\text{DRM}} @ T_J = 25^\circ\text{C}$) ($V_D = \text{Rated } V_{\text{DRM}} @ T_J = 125^\circ\text{C}$)	I_{DRM}	-	-	10 2	μA mA
Peak on-state voltage (either direction) ($I_{\text{TM}} = 11.3\text{A}$ peak, pulse width = 1 to 2 ms, duty cycle $\leq 2\%$)	V_{TM}	-	1.7	2.0	Volts
Gate trigger current (continuous dc) (main terminal voltage = 12V, $R_L = 12\Omega$) Trigger mode MT2(+),G(+); MT2(+),G(-); MT2(-),G(-)	I_{GT}	-	-	100	mA

MAC219 SERIES

SILICON BIDIRECTIONAL THYRISTORS

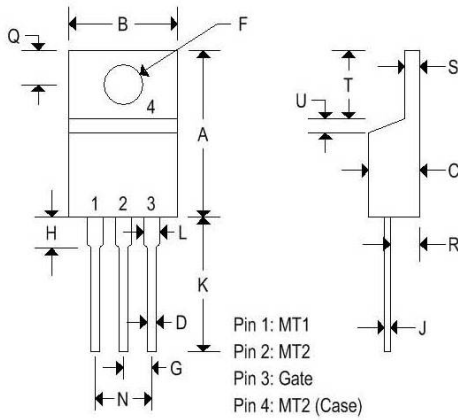
Gate trigger voltage (continuous dc) (main terminal voltage = 12V, $R_L = 100\Omega$) MT2(+),G(+) MT2(+),G(-) MT2(-),G(-) (main terminal voltage= Rated V_{DRM} , $R_L = 10k\Omega$, $T_J = 125^\circ\text{C}$) MT2(+), G(+); MT2(-), G(-); MT2(+), G(-)	V_{GT}	- - - 0.2	0.9 0.9 1.1 -	2 2 2 -	Volts
Holding current (either direction) (main terminal voltage= 12V, gate open, initiating current = 200mA)	I_H	-	-	100	mA
Rate of rise of commutation voltage (Rated V_{DRM} , $I_{T(RMS)} = 6.0\text{A}$, commutating $di/dt = 4.3\text{A/ms}$, gate unenergized, $T_C = 80^\circ\text{C}$)	$dv/dt(c)$	-	5.0	-	$\text{V}/\mu\text{s}$
Critical rate of rise of off-state voltage ($V_D = \text{Rated } V_{DRM}$, exponential voltage rise, gate open, $T_C = 25^\circ\text{C}$) ($V_D = \text{Rated } V_{DRM}$, exponential voltage rise, gate open, $T_C = 125^\circ\text{C}$)	dv/dt	500 200	- -	- -	$\text{V}/\mu\text{s}$

MECHANICAL CHARACTERISTICS

Case	TO-220AB
Marking	Alpha-numeric
Pin out	See below

MAC219 SERIES

SILICON BIDIRECTIONAL THYRISTORS



	TO-220AB			
	Inches		Millimeters	
	Min	Max	Min	Max
A	0.575	0.620	14.600	15.750
B	0.360	0.405	9.650	10.290
C	0.160	0.190	4.060	4.820
D	0.025	0.035	0.640	0.890
F	0.142	0.147	3.610	3.730
G	0.095	0.105	2.410	2.670
H	0.110	0.155	2.790	3.930
J	0.014	0.022	0.360	0.560
K	0.500	0.562	12.700	14.270
L	0.045	0.055	1.140	1.390
N	0.190	0.210	4.830	5.330
Q	0.100	0.120	2.540	3.040
R	0.060	0.110	2.040	2.790
S	0.045	0.055	1.140	1.390
T	0.235	0.255	5.970	6.480
U	-	0.050	-	1.270
V	0.045	-	1.140	-
Z	-	0.080	-	2.030

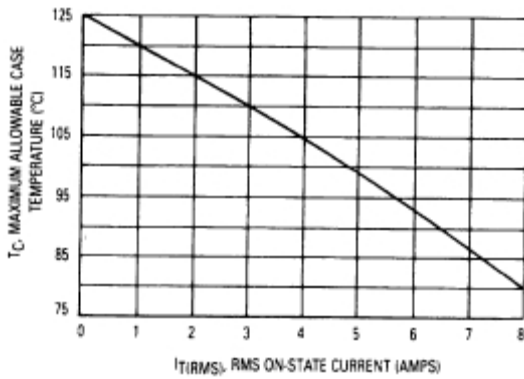


Figure 1. Current Derating

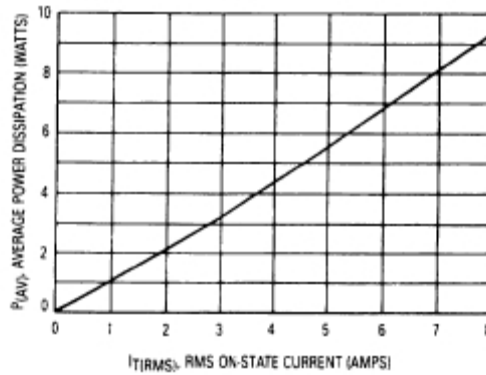


Figure 2. Power Dissipation